

LIN transceiver *MTC-30600*

1.0 Key Features

LIN-Bus Transceiver

- LIN compliant to specification revision 1.2
- I²T-100 High Voltage Technology
- Bus voltage $\pm 80V$
- Transmission rate up to 20kBaud
- SO8 Package

Protection

- Thermal shutdown
- Indefinite short-circuit protection to supply and ground
- Transients on V_{BAT} (80V)

Power saving

- Operating voltage = 4.5 to 5.5V
- Power down supply current <50 μA

EMI compatibility

- Integrated filter and hysteresis for receiver

EMC compatibility

- Integrated slope control for transmitter
- Slope control dependant from V_{bat} to enable maximum capacitive-load

General Description

The single-wire transceiver MTC-30600 is a monolithic integrated circuit in a SO-8 package. It works as an interface between the protocol controller and the physical bus.

The MTC-30600 is especially suitable to drive the bus line in LIN systems in automotive and industrial applications. Further it can be used in standard ISO9141 systems.

In order to reduce the current consumption the MTC-30600 offers a stand-by mode. A wake-up caused by a message on the bus sets the RxD output low and pulls the INH-output high

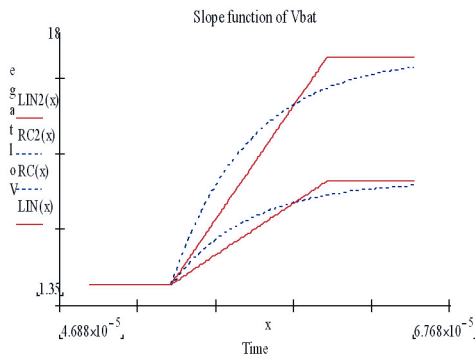
until the device is switched to normal operation mode.

The transceiver is implemented in I²T-100 technology enabling both high voltage analogue circuitry and digital functionality to co-exist on the same chip.

The MTC-30600 provides an ultra-safe solution to today's automotive In-Vehicle Networking requirements by providing unlimited short circuit protection in the event of a fault condition.

Ordering Information

Part N°: MTC-30600-I
Package: SO8
Temp. Range: -40°C...125°C



LIN transceiver *MTC-30600*

2.0 Typical application Schematic

2.1 Application schematic

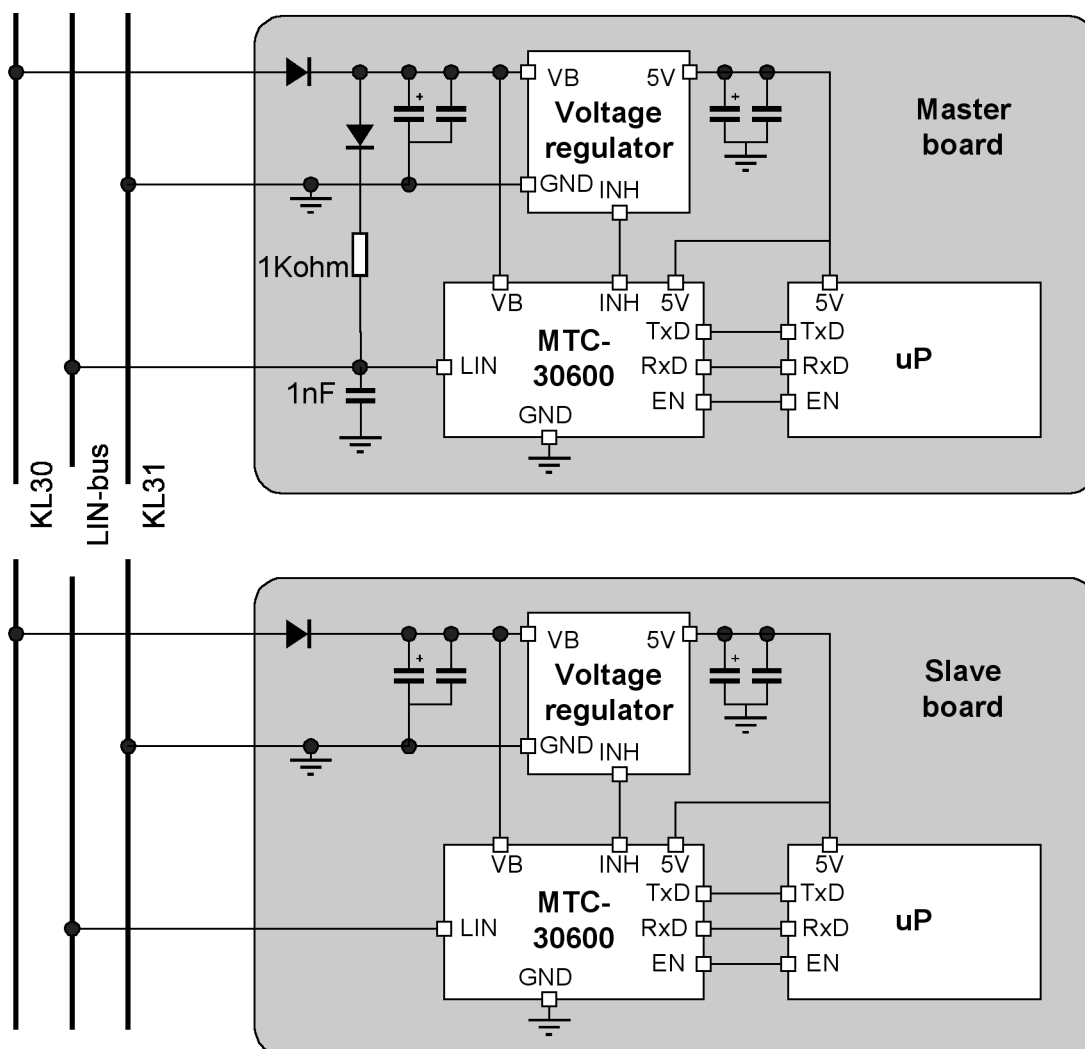


Fig.1: Typical application diagram with master and slave module

LIN transceiver *MTC-30600*

2.2 Pin description

2.2.1 Pin out (Top view)

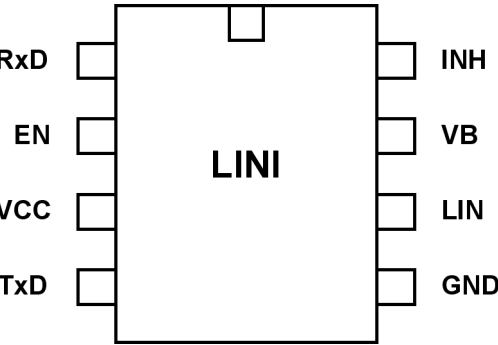


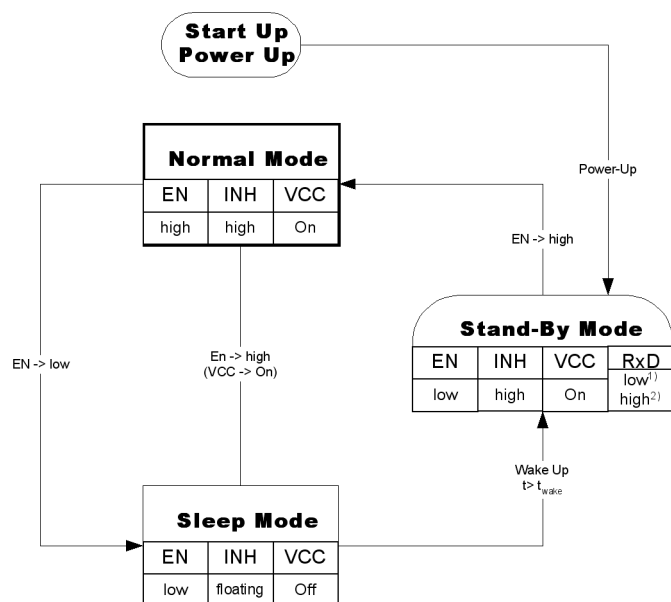
Fig.2: Pin configuration (viewed from above)

2.2.2 Pin description

Pin No	Symbol	Function
1	RxD	Receive data output; LOW in dominant state
2	EN	Enable input; transceiver in normal operation mode when HIGH; Internal 10 K Ω pull up
3	VCC	5V supply input
4	TxD	Transmit data input; LOW in dominant state; Internal 40 K Ω pull up
5	GND	Ground
6	LIN	Bus output/input; LOW in dominant state; Internal 30 K Ω pull up
7	VB	Battery supply input;
8	INH	Inhibit output; to control a voltage regulator, becomes HIGH when wake-up via LIN bus occurs

LIN transceiver *MTC-30600*

2.3 Application Information



- 1) after wake-up via bus
2) after start up

Fig.3: **State Diagram**

For fail safe reasons the MTC-30600 already has an internal pull up resistor of 30kΩ implemented. To achieve the required timings for the dominant to recessive transition of the bus signal an additional external termination resistor of 1kΩ is required. It is recommended to place this resistor in the master node. To avoid reverse currents from the bus line into the battery supply line in case of an unpowered node, it is recommended to place a diode in series to the external pull up. For small systems (low bus capacitance) the EMC performance of the system is supported by an additional capacitor of at least 1nF in the master node (see figure 1, Typical application diagram).

A capacitor of 10μF at the supply voltage input VB buffers the input voltage. In combination with the required reverse polarity diode this prevents the device from detecting power down conditions in case of negative transients on the supply line.

In order to reduce the current consumption the MTC-30600 offers a sleep operation mode. This mode is selected by switching the enable input EN low (see figure 3, state diagram). In the sleep mode a voltage regulator can be controlled via the INH output in order to minimize the current consumption of the whole application. A wake-up caused by a message on the communication bus automatically enables the voltage regulator by switching the INH output high. In parallel, the wake-up is indicated by setting the RxD output low. When entering the normal mode this wake-up flag is reset and the RxD output is released to transmit the bus data. In case the voltage regulator control input is not connected to INH output or the microcontroller is active respectively, the MTC-30600 can be set in normal operation mode without a wake-up via the communication bus.

3.0 Electrical Characteristics

3.1 Absolute maximum ratings

Note: Maximum ratings are absolute ratings; exceeding any one of these values may cause irreversible damage to the integrated circuit.

Parameter	Symbol	Limit Values		Unit	Remarks
		min	max		
Voltages					
Supply voltage	V _{CC}	-0.3	7	V	
Battery supply voltage	V _B	-0.3	40	V	
Bus input voltage	V _{bus}	-40	40	V	
INH voltage	V _{inh}	-0.3	VB+0.3	V	
Logic voltages at EN, TxD, RxD	V _I	-0.3	VCC+0.3	V	0 V < VCC < 5.5 V
Electrostatic discharge voltage at VB, Bus	V _{ESD}	-4	4	kV	human body model (100 pF via 1.5kΩ)
Electrostatic discharge voltage	V _{ESD}	-2	2	kV	human body model (100 pF via 1.5kΩ)
Temperatures					
Junction temperature	T _j	-40	150	°C	

LIN transceiver *MTC-30600*

3.2 Operating Range

Parameter	Symbol	Limit min	Values max	Unit	Remarks
Voltages					
Supply voltage	V_{CC}	4.5	5.5	V	
Battery supply voltage	V_B	8	18	V	
Junction temperature	T_j	-40	150	°C	
Thermal Shutdown (junction temperature)					
Thermal Shutdown temp	T_{JSD}	150	170	190	°C
Thermal shutdown hyst.	ΔT	–	10	–	K
Thermal resistances					
Junction ambient	R_{thj-a}	–	185	K/W	–

LIN transceiver MTC-30600

3.3 Electrical Characteristics

4.5 V < V_{CC} < 5.5 V; 8.0 V < V_B < 18 V; R_L = 500Ω ... 1 kΩ; V_{EN} > V_{EN,on}; -40 °C < T j < 125 °C; all voltages with respect to ground; positive current flowing into pin; unless otherwise specified.

Parameter	Symbol	Limit Values			Unit	Remarks
		min	typ	max		
Current Consumption						
Current consumption	I _{CC}		250	500	μA	recessive state; V TxD = V _{CC}
Current consumption	I _{VB}		100	200	μA	recessive state; V TxD = V _{CC}
Current consumption	I _{CC}		400	700	μA	dominant state; V TxD = 0 V
Current consumption	I _{VB}		1.0	1.5	mA	dominant state; V TxD = 0 V
Current consumption	I _{VB}		20	50	μA	sleep-mode
Receiver Output (pin RxD)						
HIGH level output	V RD,H	0.8 x V _{CC}		V _{CC}	V	I RD = 0.7mA ,
LOW level output	V RD,L	0		0.2 x V _{CC}	V	I RD = 0.7mA ,
Bus receiver (pin LIN)						
Receiver threshold voltage, recessive to dominant edge	V bus,rd	0.4 x V _B	0.48 x V _B		V	-8 V < V bus < Vbus,dom
Receiver threshold voltage, dominant to recessive edge	V bus,dr		0.52 x V _B	0.6 x V _B	V	V bus,rec < V bus < 20 V
Receiver hysteresis	V bus,hys	0.02 x V _B	0.04 x V _B	0.2 x V _B	mV	V bus,hys = V bus,rec - Vbus,dom
wake-up threshold voltage	V wake	0.40 x V _B		0.60 x V _B	V	
Transmission Input (pin TxD)						
HIGH level input voltage	V TD,H	H 0.7 x V _{CC}			V	recessive state
LOW level input voltage	V TD,L			0.3 x V _{CC}	V	dominant state
Pull-up resistor to VCC	R TD,pu	24		60	kΩ	
Bus transmitter (pin LIN)						
Bus recessive output voltage	V bus,rec	0.9 x V _B		V _B	V	V TxD = V _{CC}
Bus dominant output voltage	V bus,dom	0		0.15 x V _B	V	V TxD = 0 V;
Bus dominant output voltage	V bus,volt			1.4	V	V TxD = 0 V; I bus = 40mA
Bus short circuit current	I bus,sc	40	85	130	mA	V bus,short = 13.5 V
Leakage current	I bus,lk	-400	-200		μA	V _{CC} = 0V, V _B = 0V, V bus = -8 V
			5	20	μA	V _{CC} = 0V, V _B = 0V, V bus = 20 V
Bus pull up resistance	R bus	20	30	47	kΩ	
Enable input (pin EN)						
HIGH level input voltage	V EN,on	0.7 x V _{CC}			V	normal mode
LOW level input voltage	V EN,off			0.3 x V _{CC}	V	low power mode
Pull-down resistor to GND		6		15	kΩ	
Inhibit output (pin INH)						
HIGH level drop voltage	V INH		0.5	1.0	V	.I INH = - 0.15 mA
V INH = V _B - V INH						
Leakage current	I INH,lk	- 5.0		5.0	μA	sleep mode V INH = 0 V

LIN transceiver *MTC-30600*

3.3 Electrical Characteristics (cont'd)

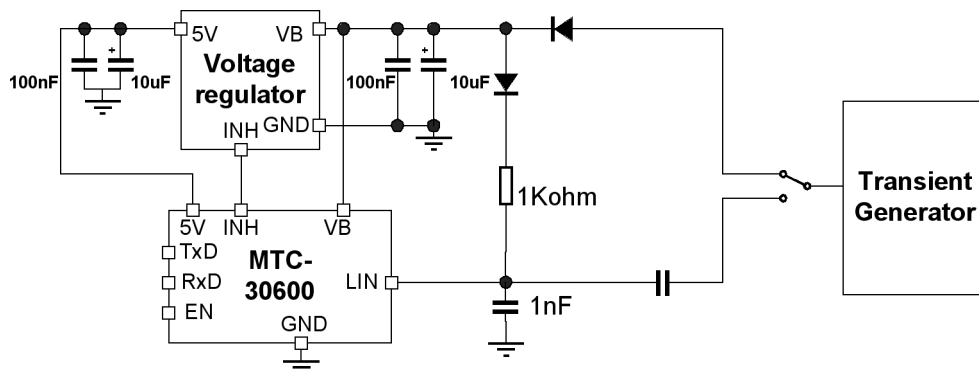
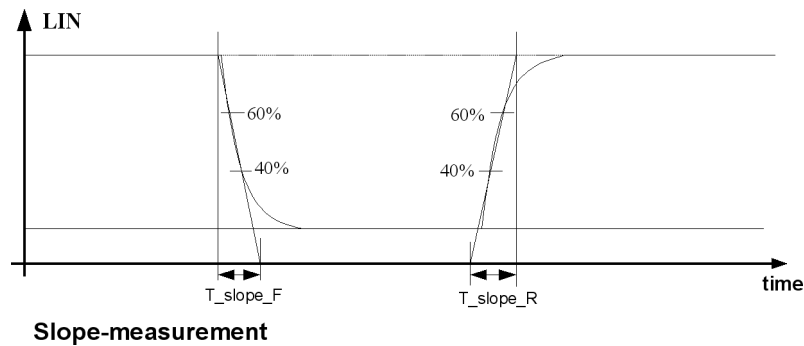
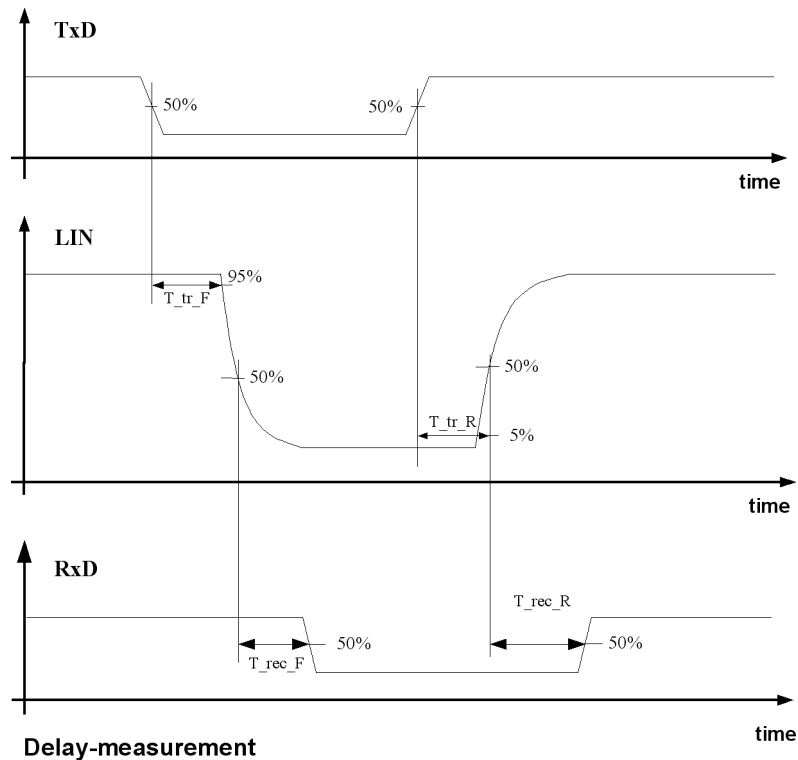
4.5 V < V_{CC} < 5.5 V; 8.0 V < V_B < 18 V; R_L = 500Ω ... 1 kΩ; V_{EN} > V_{EN,on}; -40 °C < T_j < 125 °C; all voltages with respect to ground; positive current flowing into pin; unless otherwise specified.

Load for driver definitions = 500Ω ... 1kΩ (between transceivers supply and LIN

Load for slope definitions (typical loads) = (L1) 1nF 1kΩ / (L2) 6.8nF 600Ω / (L3) 10nF 500Ω

Parameter	Symbol	Limit Values			Unit	Remarks
		min	typ	max		
Dynamic Transceiver Characteristics						
Slope time falling edge	t_slope_F	2.6		22,5	μs	See Fig 4
Slope time rising edge	t_slope_R	2.6		22,5	μs	See Fig 4
Slope time symmetry	t_slope_Sym	-4		4	μs	T_slope_Sym =t_slope_F –t_slope_R
Propagation delay TxD LOW to bus	T_tr_F		1	4	μs	See Fig 4
Propagation delay TxD HIGH to bus	T_tr_R		1	4	μs	See Fig 4
Propagation delay bus dominant to RxD LOW	T_rec_F		2	4	μs	See Fig 4 , Rxd <20pF
Propagation delay bus recessive to RxD HIGH	T_rec_R		2	4	μs	See Fig 4 , Rxd <20pF
Receiver delay symmetry	t sym, Rec	-2		2	μs	t sym,Rec = T_rec_F –T_rec_R
Transmitter delay symmetry	t sym,Tr	-2		2	μs	t sym,Tr = T_tr_F – T_tr_R
Wake-up delay time	t wake	30	100	200	μs	

LIN transceiver *MTC-30600*

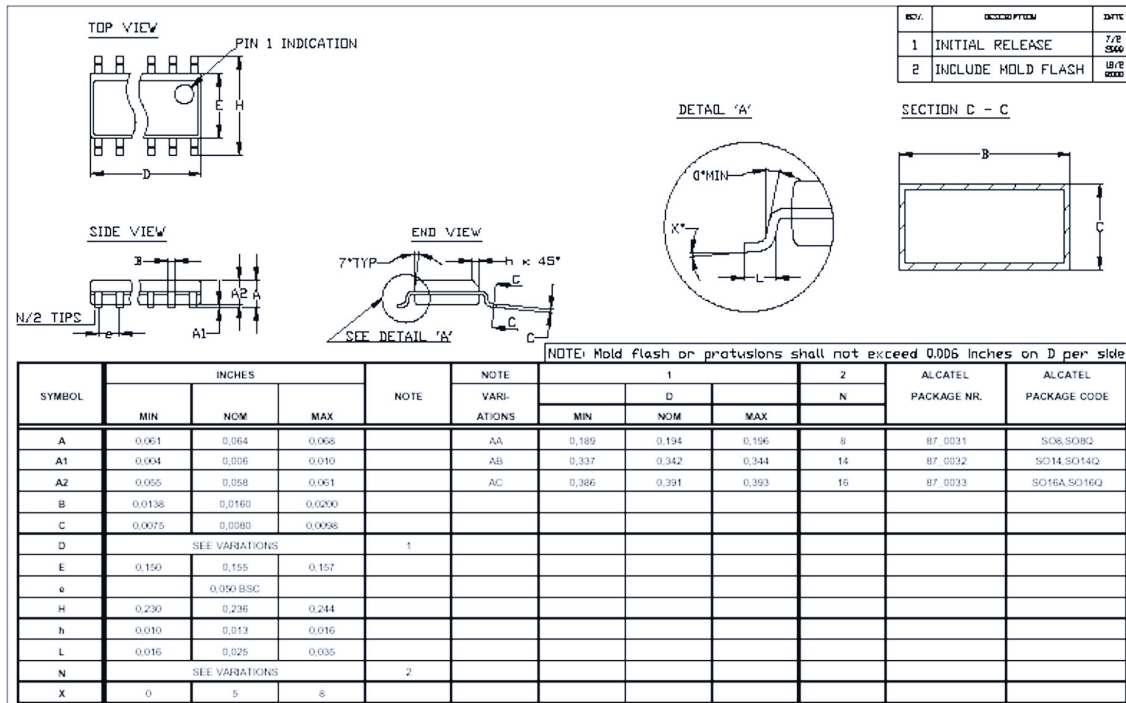


Load for driver definitions = 500Ω ... 1kΩ (between transceivers supply and LIN)
 Load for slope definitions (typical loads) = (L1) 1nF 1kΩ / (L2) 6.8nF 600Ω / (L3) 10nF 500Ω

Fig.4: Transmitter-parameters

LIN transceiver *MTC-30600*

4.0 Package Outlines



Sorts of Packing

Package outlines for tubes, trays etc. are contained in our Data Book "Package Information".

SMD = Surface Mounted Device

Dimensions in mm

LIN transceiver *MTC-30600*

AMI Semiconductor

www.amis.com

© 2002 AMI Semiconductor, Inc.
AMI Semiconductor makes no warranty for the use of its products, other than those expressly contained in the company's standard warranty contained in AMI Semiconductor's Terms and Conditions. The company assumes no responsibility for any errors which may appear in this document, reserves the right to change devices or specifications detailed herein at any time without notice, and does not make any commitment to update the information contained herein. No licenses to patents or other intellectual property of AMI Semiconductor are granted by the company in connection with the sale of AMI Semiconductor products, expressly or by implication.

